

25th RD50 Workshop (CERN)

Wednesday 19 November 2014

Defect and Material Characterization - 500/1-001 - Main Auditorium (09:40 - 12:00)

-Conveners: Ioana Pintilie

time	[id] title	presenter
09:40	[1] Nitrogen impact on vacancy aggregation in silicon single crystals	Mr KWESTARZ, Michael
10:00	[2] First results on properties and concentrations of radiation defect centers in nitrogen-enriched, high-resistivity FZ silicon	Prof. KAMINSKI, Pawel
10:20	[11] Point and extended defects in silicon induced by electron irradiation – dependence on the particle energy	Dr PINTILIE, Ioana
10:40	Coffee Break	
11:10	[20] Photoconductivity spectra as a tool for Si material stability control.	Prof. VAITKUS, Juozas
11:30	[23] Discussion on Defect and Material Characterization	Dr PINTILIE, Ioana